

Plastic-Encapsulate Diodes

SCHOTTKY BARRIER DIODE

FEATURES

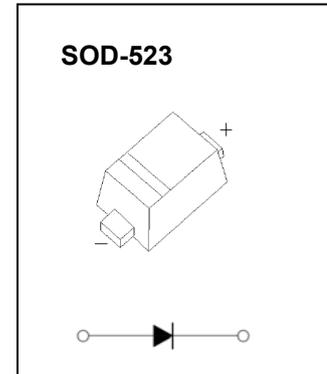
- For low-loss, fast-recovery, meter protection, bias isolation and clamping application
- Integrated diffused guard ring
- Low forward

MARKING: t



t = Device code

The marking bar indicates the cathode



Maximum Ratings (T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak reverse voltage DC reverse	V _{RM} V _R	40	V
Non-repetitive Peak surge forward current @t=8.3ms	I _{FSM}	0.8	A
Mean rectifying current	I _O	0.25	A
Power Dissipation	P _D	150	mW
Thermal Resistance from Junction to Ambient	R _{θJA}	667	°C/W
Operating Junction Temperature Range	T _J	-40~+125	°C
Storage Temperature Range	T _{stg}	-55~+150	°C

Electrical Ratings (T_a=25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse breakdown voltage	V _R	40			V	I _R =10μA
Forward voltage	V _F			350 430 520 750	mV	I _F =1mA I _F =10mA I _F =30mA I _F =100mA
Reverse current	I _R			2	μA	V _R =30V
Capacitance between terminals	C _T			6	pF	V _R =1V, f=1MHz
Reverse recovery time	t _{rr}			5	ns	I _F =10mA, I _R =10mA, I _R =1mA, R _L =100Ω

Typical Characteristics

